Silicon Carbide Power Schottky Diode

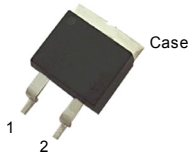
V_{RRM}	=	1200 V
V_F	=	1.7 V
I_F	=	2 A
Q_C	=	26 nC

Features

- 1200 V Schottky rectifier
- 175 °C maximum operating temperature
- Temperature independent switching behavior
- Superior surge current capability
- Positive temperature coefficient of V_F
- Extremely fast switching speeds
- Superior figure of merit Q_C/I_F

Package

- RoHS Compliant



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Advantages

- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Low reverse recovery current
- Low device capacitance
- Low reverse leakage current at operating temperature

Applications

- Power Factor Correction (PFC)
- Switched-Mode Power Supply (SMPS)
- Solar Inverters
- Wind Turbine Inverters
- Motor Drives
- Induction Heating
- Uninterruptible Power Supply (UPS)
- High Voltage Multipliers

Maximum Ratings at T_j = 175 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	I_F	$T_C \le 160$ °C	2	A
RMS forward current	$I_{F(RMS)}$	$T_C \le 160$ °C	3	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_P = 10 ms T_C = 160 °C, t_P = 10 ms	18 15	A
Non-repetitive peak forward current	$I_{F,max}$	T_C = 25 °C, t_P = 10 µs	100	A
I^2t value	$\int i^2\,dt$	T_C = 25 °C, t_P = 10 ms T_C = 160 °C, t_P = 10 ms	1.6 1.1	A^2s
Power dissipation	P_{tot}	T_C = 25 °C	65	W
Operating and storage temperature	T_j , T_{stg}		-55 to 175	°C

Electrical Characteristics at T_j = 175 °C, unless otherwise specified

Parameter	Symbol	Conditions		Values			Unit
				min.	typ.	max.	
Diode forward voltage	V_F	I_F = 2 A, T_j = 25 °C I_F = 2 A, T_j = 175 °C			1.7 2.6	2.0 3.0	V
Reverse current	I_R	V_R = 1200 V, T_j = 25 °C V_R = 1200 V, T_j = 175 °C			< 1 5	4 40	µA
Total capacitive charge	Q_C	$I_F \le I_{F,MAX}$ dI_F/dt = 200 A/µs T_j = 175 °C	V_R = 400 V V_R = 960 V		14 26		nC
Switching time	t_s		V_R = 400 V V_R = 960 V		< 17		ns
Total capacitance	C	V_R = 1 V, f = 1 MHz, T_j = 25 °C V_R = 400 V, f = 1 MHz, T_j = 25 °C V_R = 1000 V, f = 1 MHz, T_j = 25 °C			138 20 16		pF

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	2.3	°C/W

Mechanical Properties

Mounting torque	M	0.6	Nm

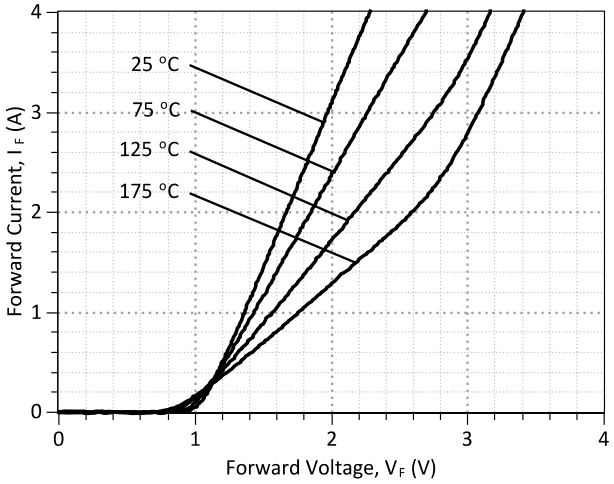


Figure 1: Typical Forward Characteristics

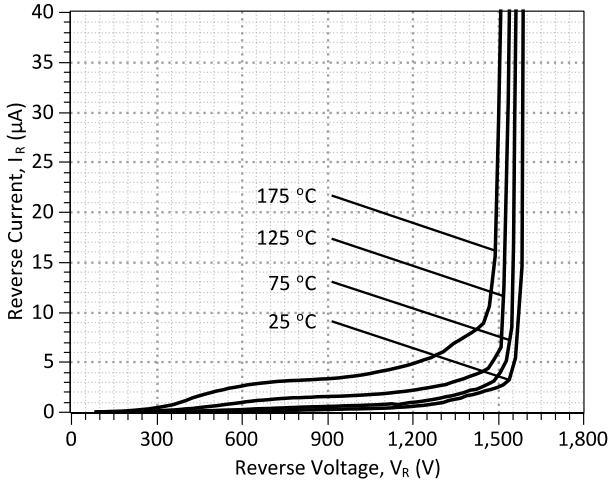


Figure 2: Typical Reverse Characteristics

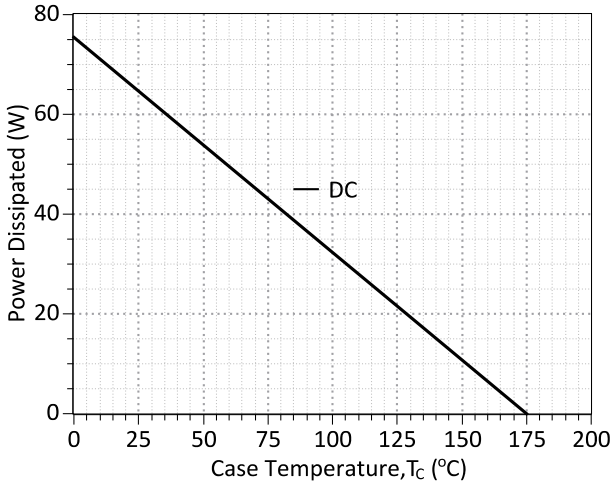


Figure 3: Power Derating Curve

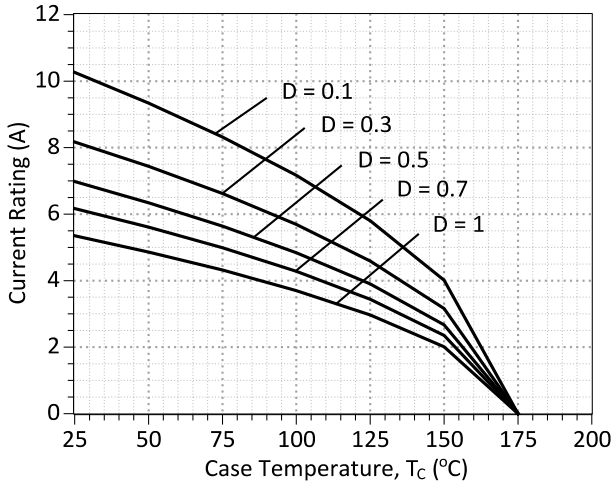


Figure 4: Current Derating Curves (D = t_P/T, t_P= 400 µs) (Considering worst case Z_{th} conditions)

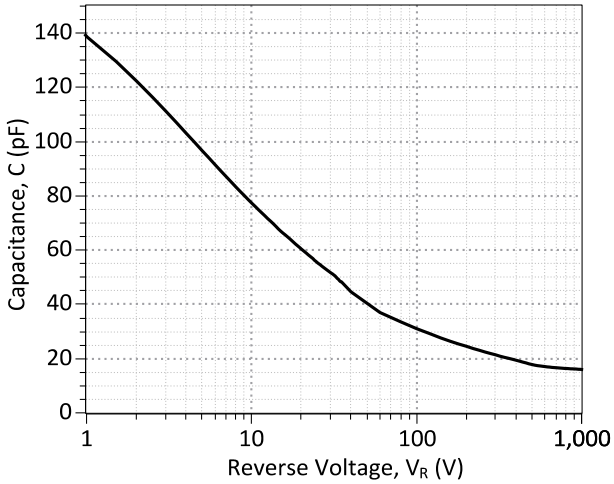


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

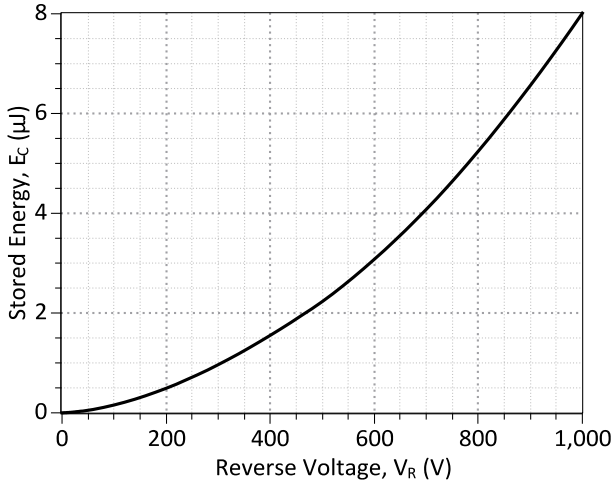


Figure 6: Typical Switching Energy vs Reverse Voltage Characteristics

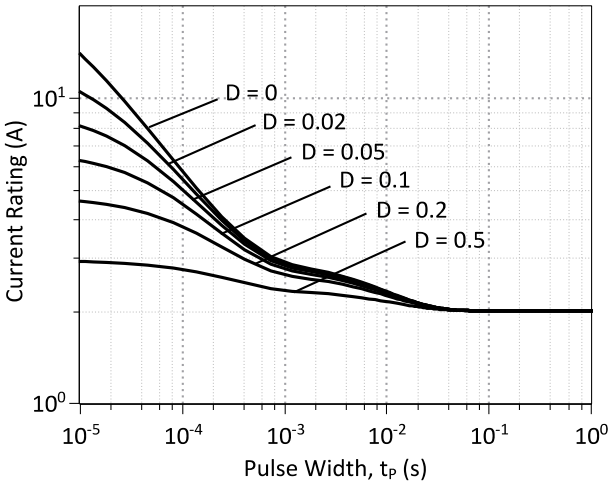


Figure 7: Current vs Pulse Duration Curves at T_C = 160 °C

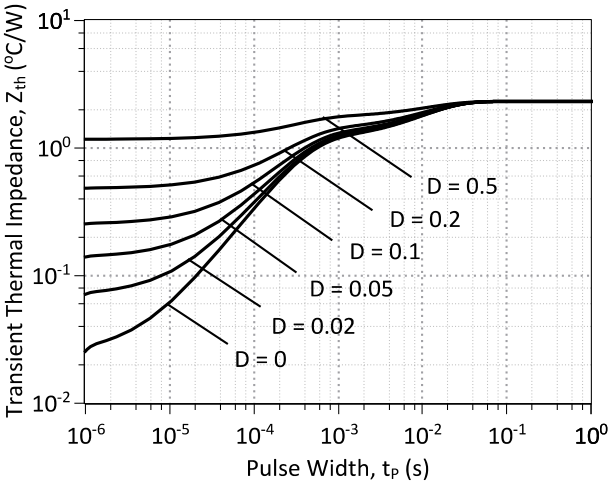
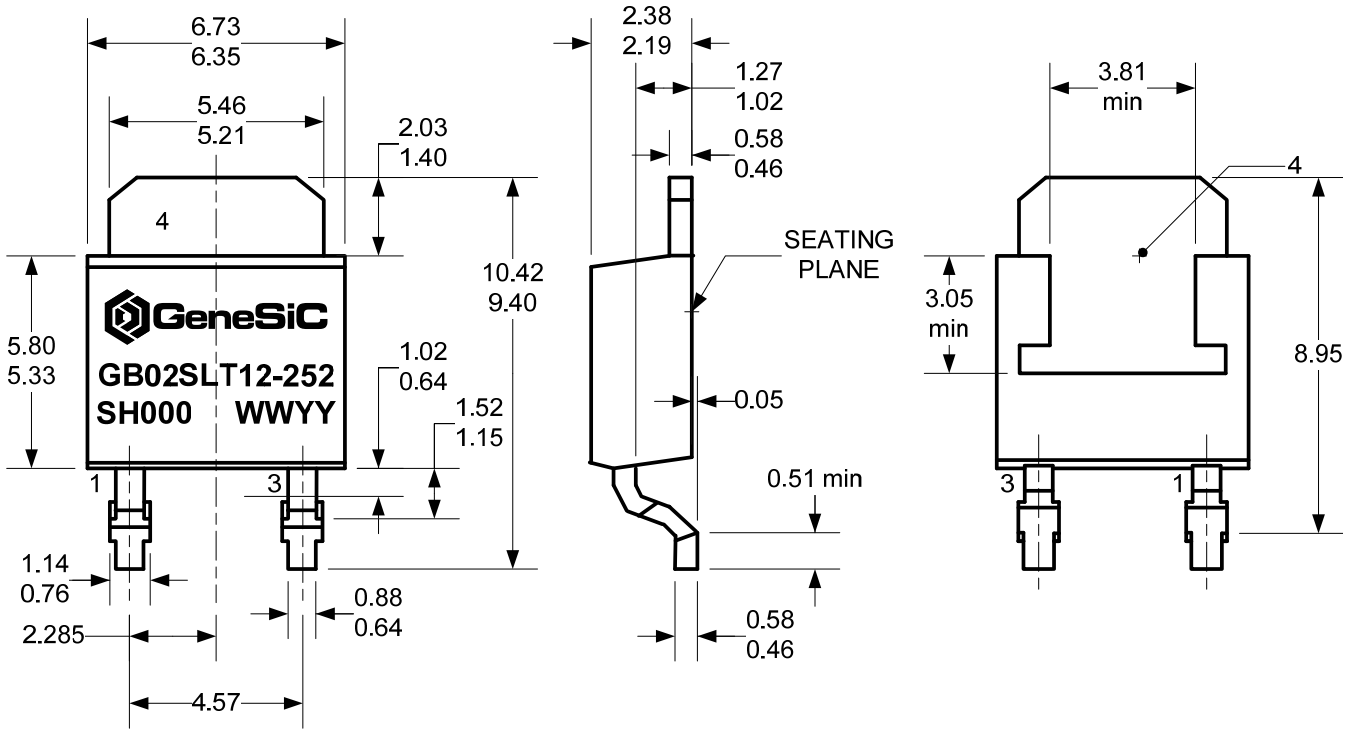


Figure 8: Transient Thermal Impedance

Package Dimensions:

TO-252 **PACKAGE OUTLINE**



NOTE
1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS
3. CONTROLLED LEAD COPLANARITY <D> 0.004 INCH MAXIMUM

Revision History			
Date	Revision	Comments	Supersedes
2012/12/18	2	Second generation update	
2012/05/22	1	Second generation release	
2010/12/13	0	Initial release	

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